

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Attorney Docket Number	41277/MJM/A717
Application Number	Not yet assigned
Filing Date	June 15, 2001
Applicant(s)	Isik C. Kizilyalli, et al.
Group Art Unit	Not yet assigned
Examiner Name	Not yet assigned

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U.S. PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

EXAMINER INITIALS	DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS

EXAMINER INITIALS	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
MG	JEON, et al., A New Poly-Si TFT with Selectively Doped Channel Fabricated by Novel Excimer Laser Annealing, IEEE International Electron Devices Meeting 2000. Technical Digest, 2000, 4 pages
MC	VERMA, et al., Formation and Control of Phosphorus Buried Layers in Silicon using a Pulsed XeCl Excimer Laser, Appl. Phys. Lett. 69 (3), 15 July 1996, pp 319-321
MC	KRAMER, et al., Resistless, Area-Selective Ultrashallow P+/N Junction Fabrication Using Projection Gas Immersion Laser Doping, Appl. Phys. Lett. 68 (17) 22 April 1996 pp 2320-2322
MG	DEJULE, Hybrid Lithography/Diffusion Technique, Emerging Technologies, Semiconductor International, January 1998, 2 pages
MC	NEUDECK, et al., Novel Silicon Epitaxy for Advanced MOSFET Devices, IEEE International Electron Devices Meeting 2000. Technical Digest, 2000, 4 pages
MC	GIUST, et al., Comparison of Excimer Laser Recrystallized Prepatterned and Unpatterned Silicon Films on SiO ₂ , J. Appl. Phys. 81 (3), 1 February 1997 pp 1204-1211
MG	SONG, et al., Single-Crystal Si Islands on SiO ₂ Obtained Via Excimer-Laser Irradiation of a Patterned Si Film, Appl. Phys. Lett. 68 (22), 27 May 1996, pp 3165-3167

EXAMINER SIGNATURE	<i>Maria Guerrero</i>	DATE CONSIDERED	9-6-02
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449

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MG

SPOSILI, et al., Sequential Lateral Solidification of Thin Silicon Films on SiO₂, Appl. Phys. Lett. 69 (19), 4 November 1996 pp2864-2866

MG

MARIUCCI, et al., Lateral Growth Control in Excimer Laser Crystallized Polysilicon, Elsevier Science, Thin Solid Films 337 (1999) pp 137-142

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